

- **Base-Emitter Resistance** ( $r_\pi$ ):

$$r_\pi = \frac{v_i}{i_b} = \frac{\Delta V_{BE}}{\Delta I_B} \equiv \left. \frac{dV_{BE}}{dI_C} \frac{dI_C}{dI_B} \right|_{V_{CE} \text{ constant}} = \frac{\beta}{g_m} \simeq \beta r_E$$

➤ For  $I_C = 1 \text{ mA}$  and  $\beta = 100$ :  $r_\pi = 2.6 \text{ k}\Omega$

- **Output Resistance** ( $r_o$ ):

$$r_o = \frac{v_{ce}}{i_c} = \left[ \frac{dI_C}{dV_{CE}} \right]^{-1} \bigg|_{V_{BE} \text{ constant}} = \frac{V_A}{I_C} = \frac{V_A}{V_T} \frac{V_T}{I_C} = \frac{1}{\eta g_m}$$

- For  $I_C = 1 \text{ mA}$ ,  $V_{AN} = 130 \text{ V}$ , and  $V_{AP} = 52 \text{ V}$ :  
 $r_0(\text{nnp}) = 130 \text{ k}\Omega$  and  $r_0(\text{pnp}) = 52 \text{ k}\Omega$
- $\eta (= V_T/V_A)$ :  $2 \times 10^{-4}$  (nnp) and  $5 \times 10^{-4}$  (pnp)
- $g_m r_0 = \eta^{-1}$

- ***Collector-Base Resistance*** ( $r_\mu$ ):

$$r_\mu = \frac{V_{ce}}{i_b} = \frac{\Delta V_{CE}}{\Delta I_B} \bigg|_{V_{BE} \text{ constant}} = \frac{dV_{CE}}{dI_C} \frac{dI_C}{dI_B} = \beta r_0$$

- ***Oversimplification*** – *actual value much higher* ( $\sim 5\text{-}10\beta r_0$ )  $> 100\text{s of M}\Omega$

- ***Emitter-Base Capacitance*** ( $C_\pi$ ):

$$C_\pi = C_{je} + C_b$$

- $C_{je}$ : ***Emitter-base depletion capacitance***

$$\approx 2C_{je0}$$

- $C_{je0}$ : ***Emitter-base depletion capacitance at zero bias***

- $C_b$ : ***Emitter-base diffusion capacitance***  
(known as ***base charging capacitance***)

$$= \tau_F g_m \quad (>> C_{je})$$

- $\tau_F$ : ***Base transit time***

- $C_\pi \uparrow$  as  $g_m \uparrow$  (***Problem!***)

- **Collector-Base Capacitance** ( $C_\mu$ ):

$$C_\mu = \frac{C_{\mu 0}}{\left(1 - \frac{V_{BC}}{V_{0,BC}}\right)^m}$$

- $C_{\mu 0}$ : **Collector-base depletion capacitance at zero bias**
- $V_{0,BC}$ : **Built-in voltage of collector-base junction**
- $m$ : **Grading coefficient** ( $1/2$  for **abrupt step junction**,  $1/3$  for **linearly graded junction**)

- *Quasi-Neutral Emitter, Base, and Collector Resistances* ( $r_e$ ,  $r_b$ , and  $r_c$ ):
  - In *IC BJT*, *emitter highest doped, followed by base*, with *collector being least doped*
  - Thus,  $r_c > r_b > r_e$
  - *Typical values*:
    - $r_e \sim 5\text{-}10\ \Omega$
    - $r_b \sim 100\text{-}200\ \Omega$
    - $r_c \sim$  can be as high as  $\text{k}\Omega$
  - *Become important only at very high frequencies*